

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>		
				Application Number		10/566522
				Filing Date		10/566522
				First Named Inventor		Yoshito Jin
				Art Unit		10566522 - GAU: 2894
Examiner Name				/Jami Valentine/		
Sheet	1	of	2	Attorney Docket Number		096790.P520

U.S. PATENT DOCUMENT

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US 3,795,977		3/12/1974	Berkenflit et al.
		US			
		US			

FOREIGN PATENT DOCUMENT

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	08-031960	A	02-02-1996	MATSUSHITA ELECTRIC IND CO LTD	Abstract
		JP	10-152397	A	06-09-1998	NIPPON TELEGRAPH & TELEPHONE CORP	Abstract
		JP	10-152398	A	06-09-1998	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	2003-077911	A	03-14-2003	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	2814416	B	08-14-1998	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	2779997	B	05-15-1998	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	08-306806	A	11-22-1996	ASAHI CHEM IND CO LTD	Abstract
		JP	07-263646	A	10-13-1995	MITSUBISHI CHEM CORP	Abstract
		JP	08-161933	A	06-21-1996	SHARP CORP	Abstract
		JP	50-004986	A	01-20-1975	INTERNATIONAL BUSINESS MACHINES CORP	
		JP	49-034390	B	09-13-1974	MATSUSHITA ELECTRIC IND CO LTD	Abstract

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Sheet	2	of	2	Attorney Docket Number		096790. P520	

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		Translation ²
		Sze, "Physics of Semiconductor Devices", Jhon Wiley and Sons, Inc., 1981		
		Matsuoka, "Applied Physics", Vol. 73, No. 9, pp.1166, 2004		Abstract
		"Development and Application of Ferroelectric Materials", edited by Tadashi Shiosaki, CMC Co., Ltd.		Abstract
		Inomata et al., "MRM Technology - from Fundamentals to LSI Applications", SIPEC		Abstract
		Amazawa et al., "Ultrathin oxidefilms deposited using electron cyclotron resonance sputter", J. Vac. Sci. Technol., B 17, No. 5		
		Matsuoka et al., "Low-temperature epitaxial growth of BaTiO3 films by radio-frequency-mode electron cyclotron resonance sputtering", J. Appl. Phys., 76(3), 1768 (1994)		
		Watazu et al., "Powder and Powder Metallurgy", No. 44, pp. 86, 1997		Abstract
		Masumoto et al., "Preparation of Bi4Ti3O12 films on a single-crystal sapphire substrate with electron cyclotron resonance plasma sputtering", Appl. Phys. Lett., 58, 243 (1991)		
		Yamaguchi et al., "Effect of Grain Size on Bi4Ti3O12 Thin Film Properties", Jpn. J. Appl. Phys., Vol. 37, (1998) pp. 5166 - 5170		
		Wild et al., "Hafnium and Zirconium silicates for advanced gate dielectrics", J. Appl. Phys., Vol. 87, No. 1, January 2000, pp. 484 - 492		

Examiner Signature	/Jami Valentine/	Date Considered	12/17/2008
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